

# MOSFET - N-Channel Shielded Gate PowerTrench® 150 V, 15 mΩ, 50 A

## NTDS015N15MC

### Features

- Shielded Gate MOSFET Technology
- Max  $R_{DS(on)}$  = 15 mΩ at  $V_{GS}$  = 10 V,  $I_D$  = 29 A
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Typical Applications

- Primary Side for 48 V Isolated Bus
- SR for MV Secondary Applications

### MAXIMUM RATINGS ( $T_J$ = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			$V_{DSS}$	150	V
Gate-to-Source Voltage			$V_{GS}$	$\pm 20$	V
Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	$T_C = 25^{\circ}\text{C}$	$I_D$	50	A
Power Dissipation $R_{\theta JC}$ (Note 2)			$P_D$	83	W
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^{\circ}\text{C}$	$I_D$	11	A
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)			$P_D$	3.8	W
Pulsed Drain Current	$T_C = 25^{\circ}\text{C}$ , $t_p = 100\text{ }\mu\text{s}$		$I_{DM}$	246	A
Operating Junction and Storage Temperature Range			$T_J$ , $T_{stg}$	-55 to +175	$^{\circ}\text{C}$
Single Pulse Drain-to-Source Avalanche Energy ( $I_L = 10\text{ A}_{pk}$ , $L = 3\text{ mH}$ )			$E_{AS}$	150	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			$T_L$	260	$^{\circ}\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

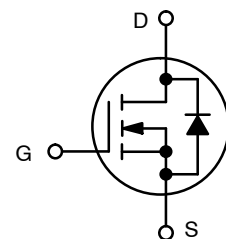
1. Surface-mounted on FR4 board using a 1 in<sup>2</sup>, 2 oz. Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.



ON Semiconductor®

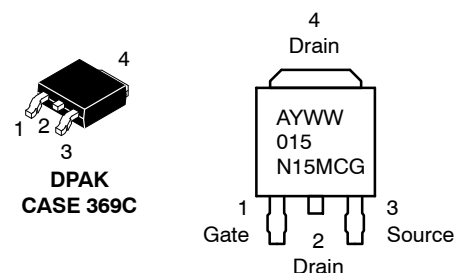
[www.onsemi.com](http://www.onsemi.com)

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
150 V	15 mΩ @ 10 V	50 A



N-CHANNEL MOSFET

### MARKING DIAGRAM



015N15MCG = Specific Device Code

A = Assembly Location

Y = Year

WW = Work Week

### ORDERING INFORMATION

Device	Package	Shipping†
NTDS015N15MCT4G	DPAK (Pb-Free)	2500 / Tube

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NTDS015N15MC

## THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 2)	$R_{\theta JC}$	1.8	°C/W
Junction-to-Ambient – Steady State (Notes 1, 2)	$R_{\theta JA}$	40	

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	150			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\text{ }\mu\text{A}$ , ref to $25^\circ\text{C}$		83		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 120\text{ V}$			1.0	$\mu\text{A}$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA

### ON CHARACTERISTICS

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 162\text{ }\mu\text{A}$	2.5		4.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 162\text{ }\mu\text{A}$ , ref to $25^\circ\text{C}$		-8.2		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 29\text{ A}$		11.8	15	m $\Omega$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 8\text{ V}, I_D = 15\text{ A}$		12.6	16.8	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 10\text{ V}, I_D = 29\text{ A}$		58		S

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 75\text{ V}$		2120		pF
Output Capacitance	$C_{OSS}$			595		
Reverse Transfer Capacitance	$C_{RSS}$			10.5		
Gate-Resistance	$R_G$			0.6	1.2	$\Omega$
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 75\text{ V}; I_D = 29\text{ A}$		27		nC
Threshold Gate Charge	$Q_{G(TH)}$			7		
Gate-to-Source Charge	$Q_{GS}$			11		
Gate-to-Drain Charge	$Q_{GD}$			4		
Plateau Voltage	$V_{GP}$			5.5		V
Output Charge	$Q_{OSS}$	$V_{DD} = 75\text{ V}, V_{GS} = 0\text{ V}$		66		nC

### SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DD} = 75\text{ V}, I_D = 29\text{ A}, R_G = 6\text{ }\Omega$		16		ns
Rise Time	$t_r$			5		
Turn-Off Delay Time	$t_{d(OFF)}$			21		
Fall Time	$t_f$			4		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = 29\text{ A}$	$T_J = 25^\circ\text{C}$		0.89	1.2	V
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, V_{DD} = 75\text{ V}$ $di_S/dt = 300\text{ A}/\mu\text{s}, I_S = 29\text{ A}$		49			ns
Reverse Recovery Charge	$Q_{RR}$			197			nC
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, V_{DD} = 75\text{ V}$ $di_S/dt = 1000\text{ A}/\mu\text{s}, I_S = 29\text{ A}$		34			ns
Reverse Recovery Charge	$Q_{RR}$			345			nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

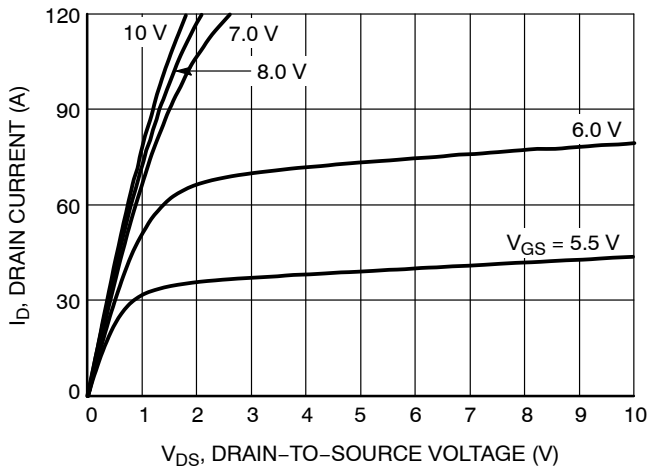


Figure 1. On-Region Characteristics

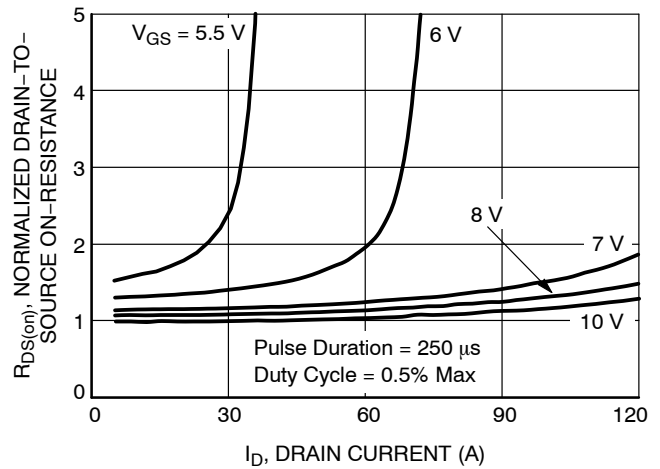


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

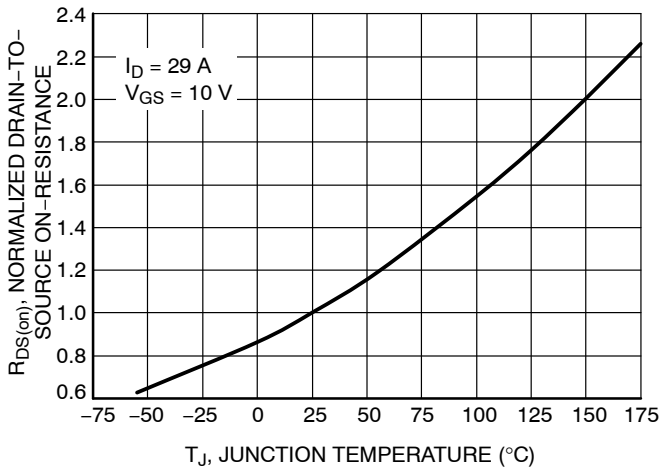


Figure 3. Normalized On-Resistance vs. Junction Temperature

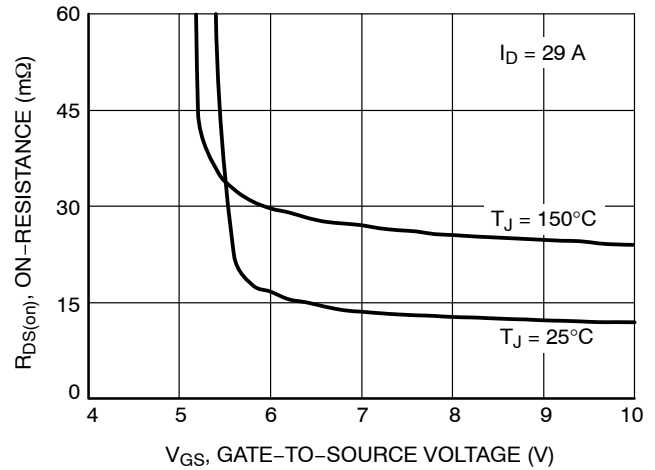


Figure 4. On-Resistance vs. Gate-to-Source Voltage

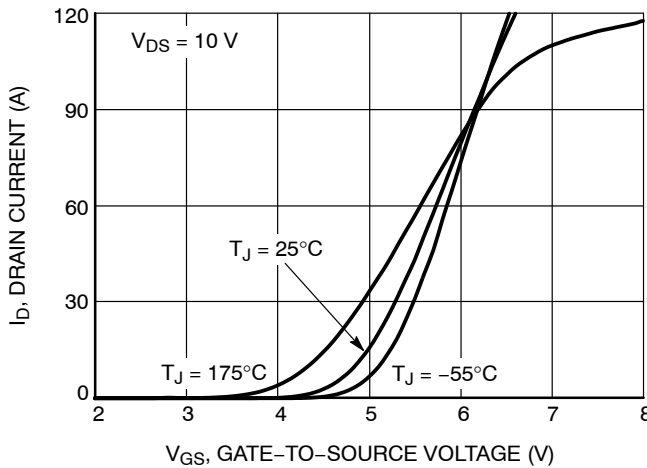


Figure 5. Transfer Characteristics

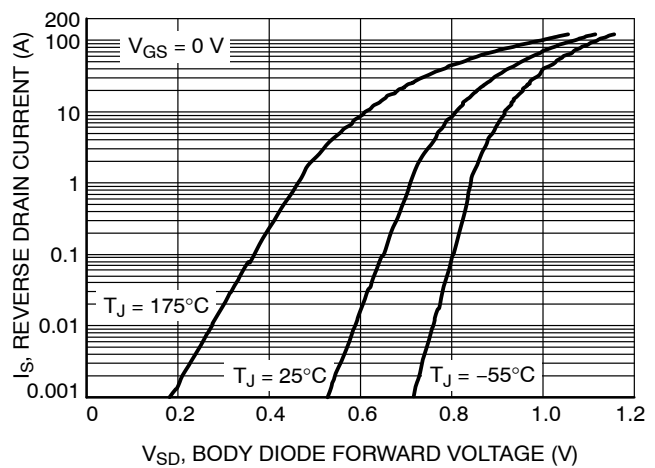


Figure 6. Source-to-Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS

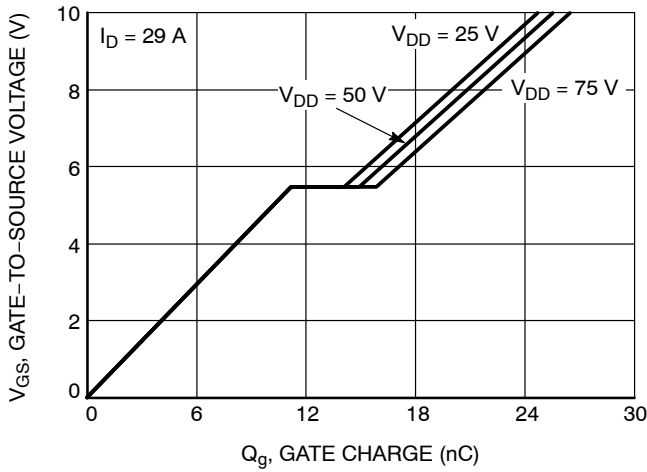


Figure 7. Gate Charge Characteristics

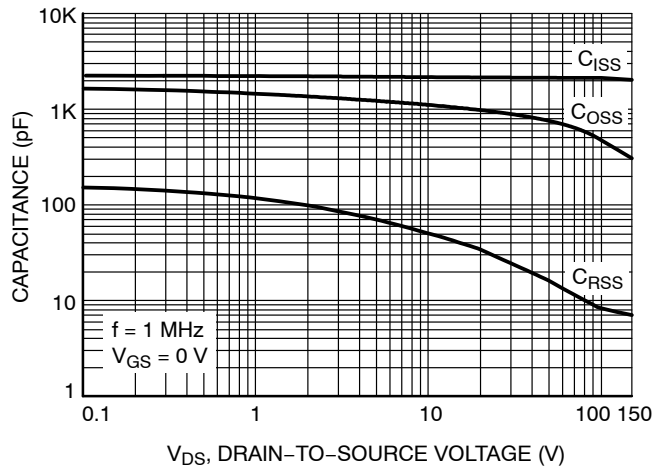


Figure 8. Capacitance vs. Drain-to-Source Voltage

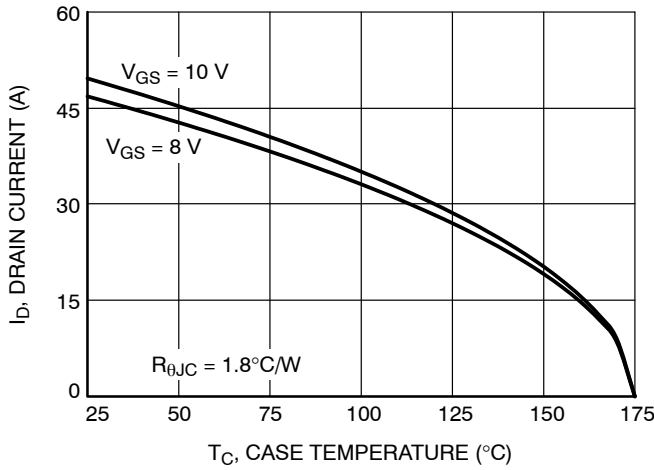


Figure 9. Drain Current vs. Case Temperature

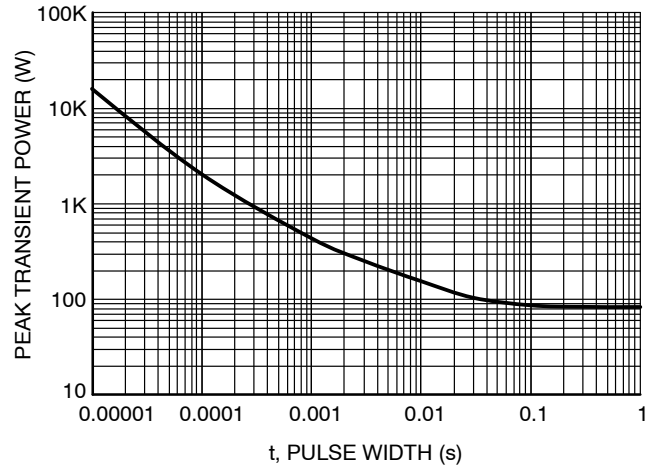


Figure 10. Peak Power

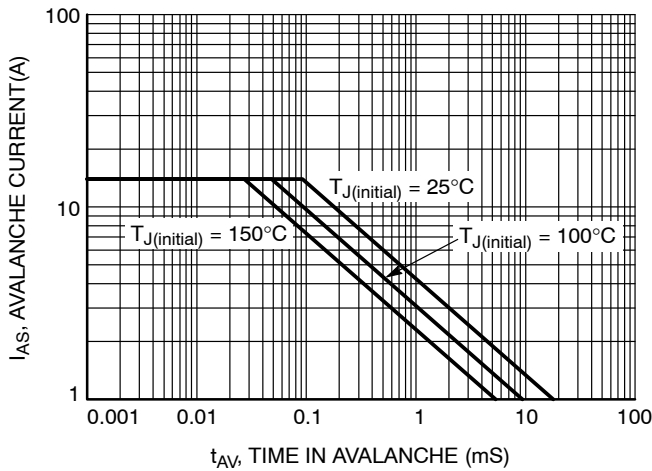


Figure 11. Unclamped Inductive Switching Capability

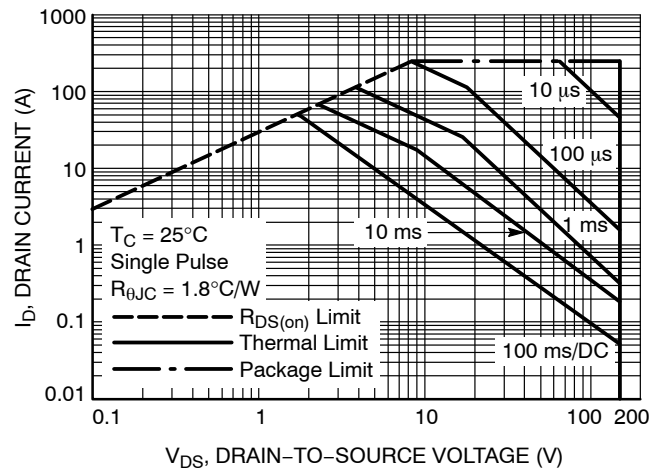
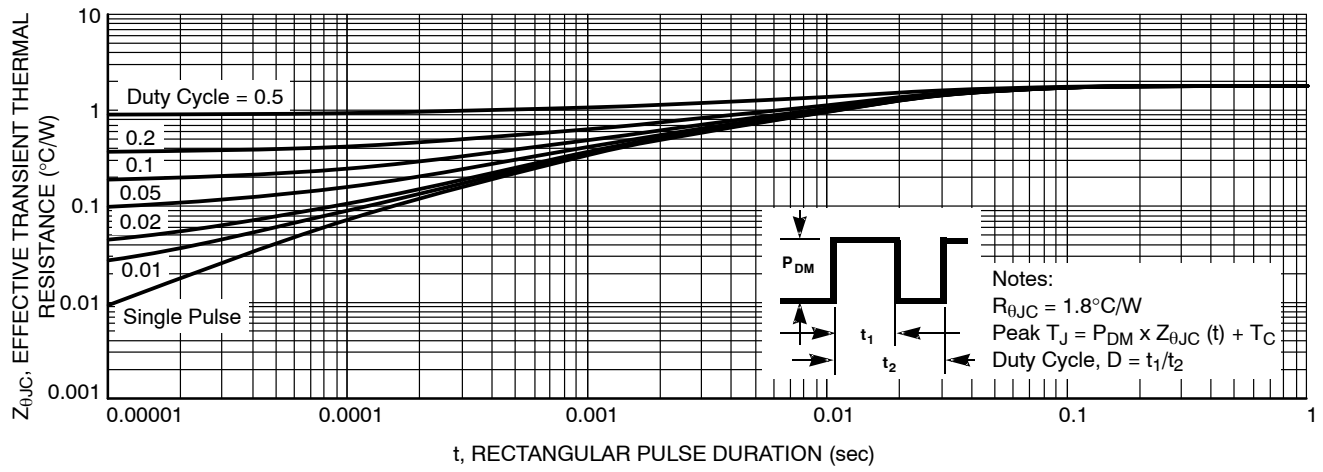


Figure 12. Forward Bias Safe Operating Area

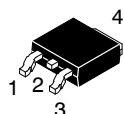
# NTDS015N15MC

## TYPICAL CHARACTERISTICS



**Figure 13. Transient Thermal Impedance**

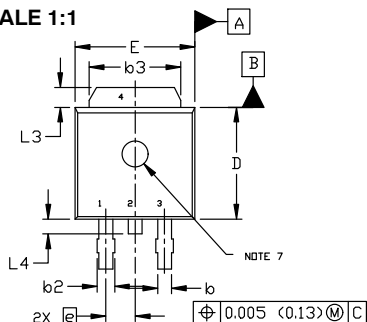
# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



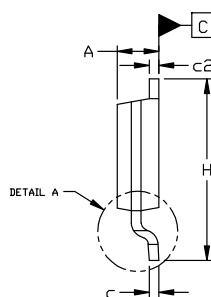
## DPAK (SINGLE GAUGE) CASE 369C ISSUE G

DATE 31 MAY 2023

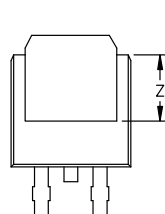
SCALE 1:1



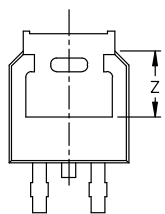
TOP VIEW



SIDE VIEW

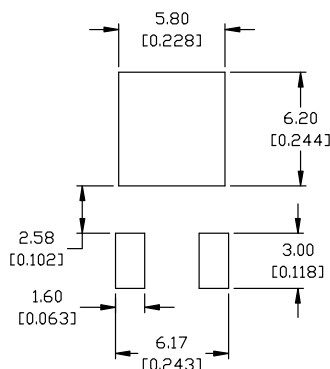


BOTTOM VIEW



BOTTOM VIEW

ALTERNATE  
CONSTRUCTIONS



### RECOMMENDED MOUNTING FOOTPRINT\*

\*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

#### STYLE 1:

PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

#### STYLE 2:

PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

#### STYLE 3:

PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

#### STYLE 4:

PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE

#### STYLE 5:

PIN 1. GATE  
2. ANODE  
3. CATHODE  
4. ANODE

#### STYLE 6:

PIN 1. MT1  
2. MT2  
3. GATE  
4. MT2

#### STYLE 7:

PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

#### STYLE 8:

PIN 1. N/C  
2. CATHODE  
3. ANODE  
4. CATHODE

#### STYLE 9:

PIN 1. ANODE  
2. CATHODE  
3. RESISTOR ADJUST  
4. CATHODE

#### STYLE 10:

PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. ANODE

### NOTES:

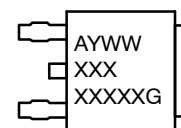
1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	----	0.040	---	1.01
Z	0.155	----	3.93	---

### GENERIC MARKING DIAGRAM\*



IC



Discrete

XXXXXX = Device Code  
A = Assembly Location  
L = Wafer Lot  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	DPAK (SINGLE GAUGE)	PAGE 1 OF 1

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